# MSKSEMI 美森科













ESD

VS

TSS

MOV

GDT

PLED

NRVB130T1G-MS

**Product specification** 





#### **FEATURES**

- Guardring for Stress Protection
- Low Forward Voltage
- 125°C Operating Junction Temperature
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Package Designed for Optimal Automated Board Assembly
- ESD Ratings: Machine Model, C;
   Human Body Model, 3
- We declare that the material of product compliance with
- RoHS requirements and Halogen Free.

#### **Reference News**

SOD-123	PIN ASSIGNMENT	MARKING
1	1	S3*

# **MAXIMUM RATINGS(Ta = 25°C)**

Parameter	Symbol	Limits	Unit	
Maximum repetitive peak reverse voltage	VRRM			
Working Peak Reverse Voltage	VRWM	30	V	
Maximum DC blocking voltage	VR			
Average Rectified Forward Current (Rated VR ) TL = 65°C	IF(AV)	1	А	
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60 Hz)	IFSM	5.5	А	
Thermal resistance (Note 1)	RθJA	230	°C/W	
Thermal redictance (Note 1)	RθJL	108	C/ <b>VV</b>	
Operating junction and storage temperature range	TJ	<b>−65 ~ +125</b>	$^{\circ}$	
Voltage Rate of Change (Rated VR )	dv/dt	1000	V/µs	

<sup>1.</sup> FR-4 or FR-5 =  $3.5 \times 1.5$  inches using a 1 inch Cu pad



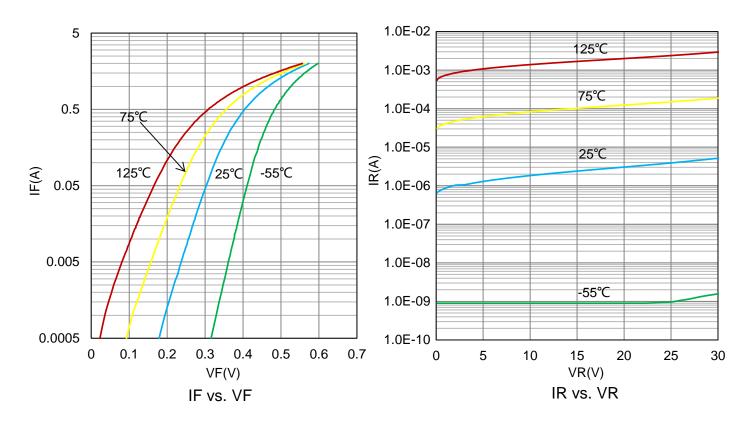
# ELECTRICAL CHARACTERISTICS (Ta= 25°C)

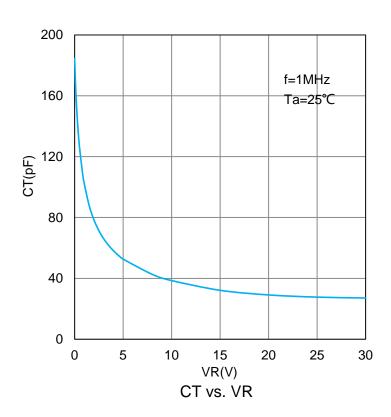
Characteristic	Symbol	Min	Тур.	Max	Unit
Reverse Breakdown Voltage (IR=500µA)	VBR	30	-	-	V
Maximum instantaneous forward Voltage(Note 2) (IF = 0.1 A, TJ = 25°C) (IF = 0.7 A, TJ = 25°C) (IF = 1.0 A, TJ = 25°C)	VF	- - -	- - 0.47	0.35 0.45 -	V
Maximum Instantaneous Reverse Current (Note 2) (VR=5V) (VR=30V)	IR	-	-	10 60	μА

<sup>2.</sup> Pulse Test: Pulse Width = 300  $\mu s, \; \text{Duty Cycle} \leqslant 2\%.$ 



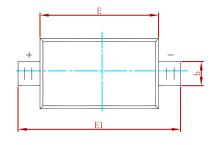
### **ELECTRICAL CHARACTERISTICS CURVES**

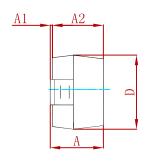


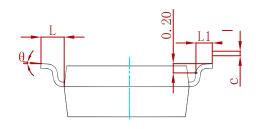




#### PACKAGE MECHANICAL DATA

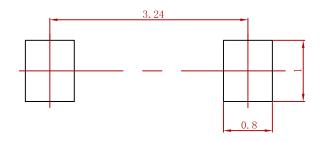






Symbol	Dimensions In MillimeterDimensions In Inches			
Syllibol	Min	Max	Min	Max
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
С	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
Е	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
Ш	0.500 REF		0.020 REF	
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

# **Suggested Pad Layout**



#### Note:

- 1. Controlling dlmenslon:in mlllmeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout Is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
NRVB130T1G-MS	SOD-123	3000



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